FEATURES

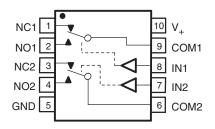
- Specified Break-Before-Make Switching
- Low ON-State Resistance (0.65 Ω Max)
- Low Charge Injection
- Excellent ON-State Resistance Matching
- Low Total Harmonic Distortion (THD)
- 1.65-V to 3.6-V Single-Supply Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78. Class II
- ESD Performance Tested Per JESD 22
 - 2000-V Human-Body Model (A114-B, Class II)
 - 1000-V Charged-Device Model (C101)

RSE PACKAGE (TOP VIEW) V₊ NC1 1 10 9 COM1 NO1 2 8 IN1 NC2 3 7 IN2 NO2 4 5 6 COM2

APPLICATIONS

- Cell Phones
- PDAs
- Portable Instrumentation
- Audio and Video Signal Routing
- Low-Voltage Data Acquisition Systems
- Communication Circuits
- Modems
- Hard Drives
- Computer Peripherals
- Wireless Terminals and Peripherals

DGS PACKAGE (TOP VIEW)



DESCRIPTION/ORDERING INFORMATION

The TS3A24157 is a dual single-pole double-throw (SPDT) analog switch that is designed to operate from 1.4 V to 3.6 V. The device offers low ON-state resistance and excellent ON-state resistance matching with the break-before-make feature, to prevent signal distortion during the transfer of a signal from one channel to another. The device has excellent total harmonic distortion (THD) performance and consumes very low power. These features make this device suitable for portable audio applications.

ORDERING INFORMATION

T _A	PACKAGE ^{(*}	1)(2)	ORDERABLE PART NUMBER	TOP-SIDE MARKING
–40°C to 85°C	QFN - RSE	Tape and reel	TS3A24157RSER	JZ0
-40 C to 65 C	VSSOP - DGS (MSOP)	Tape and reel	TS3A24157DGSR	JZ0

(1) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.

(2) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.

FUNCTION TABLE

IN	NC TO COM, COM TO NC	NO TO COM, COM TO NO		
L	ON	OFF		
Н	OFF	ON		



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



SUMMARY OF CHARACTERISTICS

 $V_{+} = 3 V, T_{A} = 25^{\circ}C$

Configuration	Dual 2:1 Multiplexer/ Demultiplexer (2× SPDT)				
Number of channels	2				
ON-state resistance (ron)	0.65 Ω max				
ON-state resistance match (Δr _{on})	0.07 Ω max				
ON-state resistance flatness (r _{on(flat)})	0.04 Ω max				
Turn-on/turn-off time (t _{ON} /t _{OFF})	35 ns/25 ns				
Break-before-make time (t _{BBM})	25 ns				
Charge injection (Q _C)	8.75 pC				
Bandwidth (BW)	50 MHz				
OFF isolation (O _{ISO})	−72 dB				
Crosstalk (X _{TALK})	−72 dB				
Total harmonic distortion (THD)	0.005%				
Power-supply current (I+)	15 nA				
Package options	10-pin QFN, 10-pin VSSOP				

Absolute Maximum Ratings(1)(2)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V ₊	Supply voltage range (3)		-0.5	3.6	V
$\begin{array}{c} V_{NC} \\ V_{NO} \\ V_{COM} \end{array}$	Analog voltage range (3)(4)(5)		-0.5	V ₊ + 0.5	V
I _{I/OK}	Analog port diode current	V_{NC} , V_{NO} , $V_{COM} < 0$	-50	50	mA
I _{NC}	ON-state switch current		-300	300	_
I _{NO} I _{COM}	ON-state peak switch current ⁽⁶⁾	V_{NC} , V_{NO} , $V_{COM} = 0$ to V_{+}	-500	500	mA
VI	Digital input voltage range		-0.5	3.6	V
I _{IK}	Digital input clamp current (3)(4)	V _I < 0	-50		mA
I ₊	Continuous current through V ₊			100	mA
I _{GND}	Continuous current through GND				mA
T _{stg}	Storage temperature range		-65	150	°C

- (1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.
- (3) All voltages are with respect to ground, unless otherwise specified.
- (4) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- (5) This value is limited to 5.5 V maximum.
- (6) Pulse at 1-ms duration <10% duty cycle.

Package Thermal Impedance

over operating free-air temperature range (unless otherwise noted)

			TYP	UNIT
0	Deckage thermal impedance (1)	DGS package	165	°C/W
θ_{JA}	θ _{JA} Package thermal impedance ⁽¹⁾	RSE package	243	C/VV

(1) The package thermal impedance is calculated in accordance with JESD 51-7.

Electrical Characteristics for 3-V Supply⁽¹⁾

 V_{+} = 2.7 V to 3.6 V, T_{A} = -40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	S	T _A	V ₊	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	V_{COM}, V_{NO}, V_{NC}					0		V ₊	٧
Peak ON	r .	$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$	Switch ON,	25°C	2.7 V		0.5	0.65	Ω
resistance	r _{peak}	$I_{COM} = -100 \text{ mA},$	See Figure 10	Full	2.7 V			0.75	12
ON-state	r _{on}	V_{NO} or $V_{NC} = 2 V$,	Switch ON,	25°C	2.7 V		0.45	0.6	Ω
resistance	on	$I_{COM} = -100 \text{ mA},$	See Figure 10	Full	Z.7 V			0.65	22
ON-state	Δ	V_{NO} or $V_{NC} = 2 \text{ V}, 0.8 \text{ V},$	Switch ON,	25°C	0.7.1/		0.05	0.07	
resistance match between channels	∆r _{on}	$I_{COM} = -100 \text{ mA},$	See Figure 10	Full	2.7 V			0.08	Ω
ON-state resistance flatness	atness ron(flat)	$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$ $I_{COM} = -100 \text{ mA},$	Switch ON, See Figure 10	25°C	2.7 V		0.025		Ω
		V_{NO} or $V_{NC} = 2 \text{ V}, 0.8 \text{ V},$		25°C			0.01	0.04	
		$I_{COM} = -100 \text{ mA},$ See Figure 10	Full				0.1		
NC, NO	INO NO N	25°C		-50		50			
OFF leakage current	I _{NO(OFF)}	or V_{NC} or $V_{NO} = 3 \text{ V}$, $V_{COM} = 1 \text{ V}$,	See Figure 11	Full	3.6 V	-250		250	nA
NC, NO	I _{NC(ON)} ,	V_{NC} or $V_{NO} = 1 V$, $V_{COM} = Open$,	Switch ON.	25°C		-50		50	
ON leakage current	I _{NO(ON)}	or V_{NC} or $V_{NO} = 3 \text{ V}$, $V_{COM} = \text{Open}$,	See Figure 12	Full	3.6 V	-400		400	nA
COM		V_{NC} or V_{NO} = Open, V_{COM} = 1 V,	Switch ON.	25°C		-50		50	
ON leakage current	I _{COM(ON)}	or V_{NC} or V_{NO} = Open, V_{COM} = 3 V,	See Figure 12	Full	3.6 V	-400		400	nA
Digital Control Inpu	ıts (IN1, IN2) ⁽²⁾								
Input logic high	V _{IH}			Full		1.4			V
Input logic low	V _{IL}			Full				0.5	V
Input leakage	I I	V = 3.6 V or 0	25°C	3.6 V	-50	5	50	nA	
current	I _{IH} , I _{IL}	$V_1 = 3.6 \text{ V or } 0$		Full	3.0 V	-150		150	IIA

The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum All unused digital inputs of the device must be held at V_+ or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

TS3A24157 $0.65-\Omega$ DUAL SPDT ANALOG SWITCH DUAL-CHANNEL 2:1 MULTIPLEXER/DEMULTIPLEXER





Electrical Characteristics for 3-V Supply⁽¹⁾ (Continued)

 $V_{+} = 2.7 \text{ V to } 3.6 \text{ V}, T_{A} = -40^{\circ}\text{C} \text{ to } 85^{\circ}\text{C} \text{ (unless otherwise noted)}$

PARAMETER	SYMBOL	TEST CON	DITIONS	T _A	V ₊	MIN	TYP	MAX	UNIT
Dynamic									
		V V	C 25 x 5	25°C	3 V		20	35	
Turn-on time	t _{ON}	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	C _L = 35 pF, See Figure 14	Full	2.7 V to 3.6 V			40	ns
		\/ - \/	$C_1 = 35 pF$,	25°C	3 V		12	25	
Turn-off time	t _{OFF}	$V_{COM} = V_+,$ $R_L = 50 \Omega,$: 50 Ω, See Figure 14	Full	2.7 V to 3.6 V			30	ns
Break-before-		W W	$C_1 = 35 pF$,	25°C	3 V	1	10	25	
make time	t _{BBM}	$V_{NC} = V_{NO} = V_+,$ $R_L = 50 \Omega,$	See Figure 15	Full	2.7 V to 3.6 V	0.5		30	ns
Charge injection	Q _C	$V_{GEN} = 0,$ $R_{GEN} = 0,$	C _L = 1 nF, See Figure 19	25°C	3 V		8.75		pC
NC, NO OFF capacitance	$C_{NC(OFF)}, \\ C_{NO(OFF)}$	V_{NC} or $V_{NO} = V_{+}$ or GND, Switch OFF,	See Figure 13	25°C	3 V		50		pF
NC, NO ON capacitance	C _{NC(ON)} , C _{NO(ON)}	V_{NC} or $V_{NO} = V_{+}$ or GND, Switch ON,	See Figure 13	25°C	3 V		140		pF
COM ON capacitance	C _{COM(ON)}	V _{COM} = V ₊ or GND, Switch ON,	See Figure 13	25°C	3 V		140		pF
Digital input capacitance	C _I	$V_I = V_+ \text{ or GND},$	See Figure 13	25°C	3 V		2		pF
Bandwidth	BW	$R_L = 50 \Omega$, Switch ON,	See Figure 16	25°C	3 V		50		MHz
OFF isolation	O _{ISO}	$R_L = 50 \Omega$, f = 1 MHz,	See Figure 17	25°C	3 V		-72		dB
Crosstalk	X _{TALK}	$R_L = 50 \Omega$, f = 1 MHz,	See Figure 18	25°C	3 V		-72		dB
Total harmonic distortion	THD	$R_L = 600 \Omega,$ $C_L = 50 pF,$	f = 20 Hz to 20 kHz, See Figure 20	25°C	3 V		0.005		%
Supply									
Positive supply current	l ₊	V _I = V ₊ or GND		25°C Full	3.6 V		15	200 1200	nA

⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

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Electrical Characteristics for 2.5-V Supply⁽¹⁾

 $V_{+} = 2.3 \text{ V}$ to 2.7 V, $T_{A} = -40^{\circ}\text{C}$ to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	S	T _A	V ₊	MIN	TYP	MAX	UNIT
Analog Switch						•		·	
Analog signal range	V_{COM}, V_{NO}, V_{NC}					0		V ₊	V
Peak ON	r .	$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$	Switch ON,	25°C	2.3 V		0.55	0.75	Ω
resistance	r _{peak}	$I_{COM} = -8 \text{ mA},$	See Figure 10	Full	2.3 V			0.9	12
ON-state	r _{on}	V_{NO} or $V_{NC} = 1.8 \text{ V}$,	Switch ON,	25°C	2.3 V		0.56	0.75	Ω
resistance	on	$I_{COM} = -8 \text{ mA},$	See Figure 10	Full	2.5 V			0.85	32
ON-state	Δ.,	V_{NO} or $V_{NC} = 1.8 \text{ V}, 0.8 \text{ V},$	Switch ON,	25°C	0.0.1/		0.1	0.15	0
resistance match between channels	Δr _{on}	$I_{COM} = -8 \text{ mA},$	See Figure 10	Full	2.3 V			0.15	Ω
ON-state		$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$ $I_{COM} = -8 \text{ mA},$	Switch ON, See Figure 10	25°C			0.1	0.15	Ω
resistance flatness	r _{on(flat)}	V_{NO} or $V_{NC} = 0.8 \text{ V}, 1.8 \text{ V},$	Switch ON,	25°C	2.3 V			0.17	
		$I_{COM} = -8 \text{ mA},$ See Figure 10	Full				0.2		
NC, NO	I _{NC(OFF)} ,	V_{NC} or $V_{NO} = 0.5 \text{ V}$, $V_{COM} = 2.2 \text{ V}$,	Switch OFF,	25°C	07.7	-50		50	
OFF leakage current	I _{NO(OFF)}	or V_{NC} or $V_{NO} = 2.2 \text{ V}$, $V_{COM} = 0.5 \text{ V}$,	See Figure 11	Full	2.7 V	-250		250	nA
NC, NO	I _{NC(ON)} ,	V_{NC} or $V_{NO} = 0.5 \text{ V}$, $V_{COM} = \text{Open}$,	Switch ON.	25°C		-50		50	
ON leakage current	I _{NO(ON)}	or V_{NC} or $V_{NO} = 2.2 \text{ V}$, $V_{COM} = \text{Open}$,	See Figure 12	Full	2.7 V	-400		400	nA
COM	_	V_{NC} or V_{NO} = Open, V_{COM} = 0.5 V,	Switch ON.	25°C		-50		50	
ON leakage current	I _{COM(ON)}	or V_{NC} or V_{NO} = Open, V_{COM} = 2.2 V,	See Figure 12	Full	2.7 V	-400		400	nA
Digital Control Inpu	uts (IN1, IN2) ⁽²⁾)							
Input logic high	V _{IH}			Full		1.25			V
Input logic low	V _{IL}			Full				0.5	V
Input leakage	1 1	V 27 V or 0	25°C	2.7 V	-50		50	nA	
current	I _{IH} , I _{IL}	$V_1 = 2.7 \text{ V or } 0$		Full	2.1 V	-50		50	IIA

The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum All unused digital inputs of the device must be held at V_+ or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

TS3A24157 0.65-Ω DUAL SPDT ANALOG SWITCH DUAL-CHANNEL 2:1 MULTIPLEXER/DEMULTIPLEXER





Electrical Characteristics for 2.5-V Supply⁽¹⁾ (Continued)

 $V_{+} = 2.3 \text{ V}$ to 2.7 V, $T_{A} = -40^{\circ}\text{C}$ to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CON	NDITIONS	T _A	V ₊	MIN	TYP	MAX	UNIT
Dynamic									
		V V	C 25 pF	25°C	2.5 V		23	45	
Turn-on time	t _{ON}	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	C _L = 35 pF, See Figure 14	Full	2.3 V to 2.7 V			50	ns
		\/ - \/	C _L = 35 pF,	25°C	2.5 V		17	27	
Turn-off time	t _{OFF}	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	See Figure 14	Full	2.3 V to 2.7 V			30	ns
Break-before-		\ \ \ \ - \\ \ - \\	0 05 - 5	25°C	2.5 V	2	14	30	
make time	t _{BBM}	$V_{NC} = V_{NO} = V_+,$ $R_L = 50 \Omega,$	C _L = 35 pF, See Figure 15	Full	2.3 V to 2.7 V	1		35	ns
Charge injection	Q_{C}	$V_{GEN} = 0,$ $R_{GEN} = 0,$	C _L = 1 nF, See Figure 19	25°C	2.5 V		8		рС
NC, NO OFF capacitance	$C_{NC(OFF)}, \\ C_{NO(OFF)}$	V_{NC} or $V_{NO} = V_{+}$ or GND, Switch OFF,	See Figure 13	25°C	2.5 V		50		pF
NC, NO ON capacitance	C _{NC(ON)} , C _{NO(ON)}	V_{NC} or $V_{NO} = V_{+}$ or GND, Switch ON,	See Figure 13	25°C	2.5 V		140		pF
COM ON capacitance	C _{COM(ON)}	V _{COM} = V ₊ or GND, Switch ON,	See Figure 13	25°C	2.5 V		140		pF
Digital input capacitance	C _I	$V_I = V_+ \text{ or GND},$	See Figure 13	25°C	2.5 V		2		pF
Bandwidth	BW	$R_L = 50 \Omega$, Switch ON,	See Figure 16	25°C	2.5 V		50		MHz
OFF isolation	O _{ISO}	$R_L = 50 \Omega$, f = 1 MHz,	See Figure 17	25°C	2.5 V		-72		dB
Crosstalk	X _{TALK}	$R_L = 50 \Omega$, f = 1 MHz,	See Figure 18	25°C	2.5 V		-72		dB
Total harmonic distortion	THD	$R_L = 600 \Omega,$ $C_L = 50 pF,$	f = 20 Hz to 20 kHz, See Figure 20	25°C	2.5 V		0.006		%
Supply	·								
Positive supply		$V_1 = V_+$ or GND		25°C	2.7 V		10	150	nA
current	I ₊	VI = V+ OI GIND		Full	2.1 V			700	IIA

⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

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Electrical Characteristics for 1.8-V Supply⁽¹⁾

 V_{+} = 1.65 V to 1.95 V, T_{A} = -40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	TEST CONDITIONS		V ₊	MIN	TYP	MAX	UNIT
Analog Switch						•		·	
Analog signal range	V_{COM}, V_{NO}, V_{NC}					0		V ₊	V
Peak ON	r .	$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$	Switch ON,	25°C	1.65 V	8.0		1.25	Ω
resistance	r _{peak}	$I_{COM} = -2 \text{ mA},$	See Figure 10	Full	1.00 V			1.4	32
ON-state	r _{on}	V_{NO} or $V_{NC} = 1.5 V$,	Switch ON,	25°C	1.65 V	0.6		0.95	Ω
resistance	on	$I_{COM} = -2 \text{ mA},$	See Figure 10	Full	1.05 V			1	32
ON-state				25°C		0.1		0.15	
resistance match between channels	Δr_{on}	V_{NO} or $V_{NC} = 0.6 \text{ V}$, 1.5 V, $I_{COM} = -2 \text{ mA}$,	Switch ON, See Figure 10	Full	1.65 V			0.15	Ω
ON-state		$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$ $I_{COM} = -2 \text{ mA},$	Switch ON, See Figure 10	25°C	1 65 V		0.35	0.13	
resistance flatness	r _{on(flat)}	V_{NO} or $V_{NC} = 0.6 \text{ V}$, 1.5 V, Switch ON, $I_{COM} = -8 \text{ mA}$, See Figure 10	Switch ON,	25°C	1.65 V		0.05		Ω
namess			Full				0.2		
NC, NO	I _{NC(OFF)} ,	V_{NC} or $V_{NO} = 0.3 \text{ V}$, $V_{COM} = 1.65 \text{ V}$,	Switch OFF,	25°C		-50		50	
OFF leakage current	I _{NO(OFF)}	or V_{NC} or $V_{NO} = 1.65 \text{ V}$, $V_{COM} = 0.3 \text{ V}$,	See Figure 11	Full	1.65	-250		250	nA
NC, NO	I _{NC(ON)} ,	V_{NC} or $V_{NO} = 0.3 \text{ V}$, $V_{COM} = \text{Open}$,	Switch ON.	25°C	4.05.1/	-50		50	
ON leakage current	I _{NO(ON)}	or V_{NC} or $V_{NO} = 1.65 \text{ V}$, $V_{COM} = \text{Open}$,	See Figure 12	Full	1.95 V	-400		400	nA
COM		V_{NC} or V_{NO} = Open, V_{COM} = 0.3 V,	Switch ON.	25°C		-50		50	
ON leakage current	I _{COM(ON)}	or V_{NC} or V_{NO} = Open, V_{COM} = 1.65 V,	See Figure 12	Full	1.95 V	-400		400	nA
Digital Control In	puts (IN1, IN2)	(2)							
Input logic high	V _{IH}			Full		1			V
Input logic low	V _{IL}			Full				0.4	V
Input leakage		ane	25°C	1.05.\/		0	50) nA	
current	I _{IH} , I _{IL}	$V_{I} = 1.95 \text{ V or } 0$		Full	1.95 V			150	IIA

⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

⁽²⁾ All unused digital inputs of the device must be held at V₊ or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

TS3A24157 0.65-Ω DUAL SPDT ANALOG SWITCH DUAL-CHANNEL 2:1 MULTIPLEXER/DEMULTIPLEXER



SCDS208A-JUNE 2007-REVISED SEPTEMBER 2007

Electrical Characteristics for 1.8-V Supply⁽¹⁾ (Continued)

 $V_{+} = 1.65 \text{ V}$ to 1.95 V, $T_{A} = -40^{\circ}\text{C}$ to 85°C (unless otherwise noted)

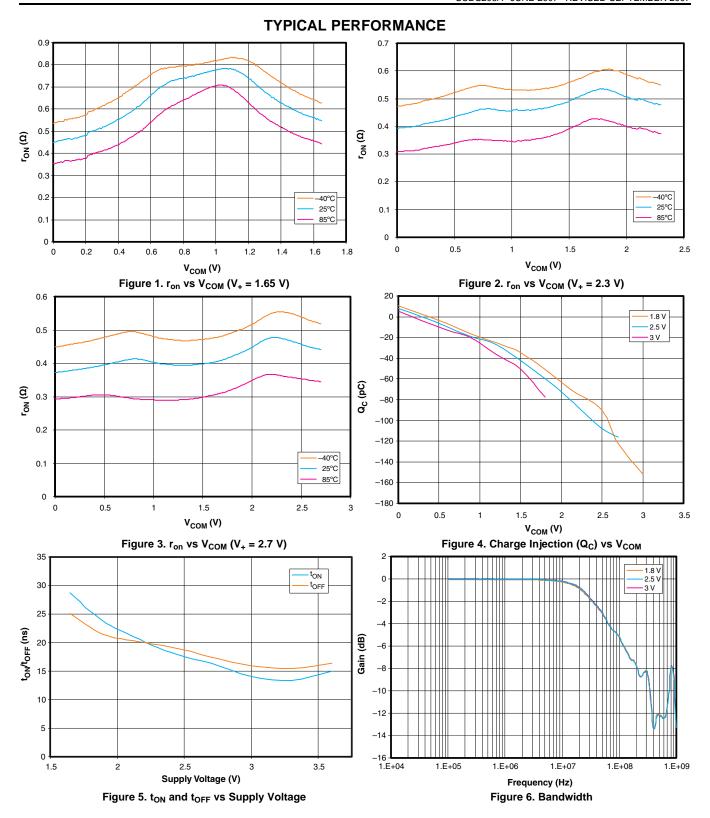
PARAMETER	SYMBOL	TEST CON	DITIONS	T_A	V ₊	MIN	TYP	MAX	UNIT
Dynamic									
		V V	0 25 = 5	25°C	1.8 V		33	75	
Turn-on time	t _{ON}	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	C _L = 35 pF, See Figure 14	Full	1.65 V to 1.95 V			80	ns
		\/ - \/	$C_1 = 35 \text{ pF},$	25°C	1.8 V		24	35	
Turn-off time	t _{OFF}	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	See Figure 14	Full	1.65 V to 1.95 V			40	ns
Break-before-		W W	C 25 pF	25°C	1.8 V	2	20	40	
make time	t _{BBM}	$V_{NC} = V_{NO} = V_{+},$ $R_{L} = 50 \Omega,$	C _L = 35 pF, See Figure 15	Full	1.65 V to 1.95 V	1		50	ns
Charge injection	Q _C	$V_{GEN} = 0,$ $R_{GEN} = 0,$	C _L = 1 nF, See Figure 19	25°C	1.8 V		4		рС
NC, NO OFF capacitance	$C_{NC(OFF)}, \\ C_{NO(OFF)}$	V_{NC} or $V_{NO} = V_{+}$ or GND, Switch OFF,	See Figure 13	25°C	1.8 V		50		pF
NC, NO ON capacitance	C _{NC(ON)} , C _{NO(ON)}	V_{NC} or $V_{NO} = V_{+}$ or GND, Switch ON,	See Figure 13	25°C	1.8 V		140		pF
COM ON capacitance	C _{COM(ON)}	V _{COM} = V ₊ or GND, Switch ON,	See Figure 13	25°C	1.8 V		140		pF
Digital input capacitance	C _I	$V_1 = V_+ \text{ or GND},$	See Figure 13	25°C	1.8 V		2		pF
Bandwidth	BW	$R_L = 50 \Omega$, Switch ON,	See Figure 16	25°C	1.8 V		48		MHz
OFF isolation	O _{ISO}	$R_L = 50 \Omega$, f = 1 MHz,	See Figure 17	25°C	1.8 V		-73		dB
Crosstalk	X _{TALK}	$R_L = 50 \Omega$, f = 1 MHz,	See Figure 18	25°C	1.8 V		-72		dB
Total harmonic distortion	THD	$R_L = 600 \Omega,$ $C_L = 50 pF,$	f = 20 Hz to 20 kHz, See Figure 20	25°C	1.8 V				%
Supply				•					
Positive supply	I ₊	$V_I = V_+$ or GND		25°C	1.95 V		10	100	nΛ
current	'+	VI - V+ OI GIND		Full	1.95 V			600	nA

⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

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TYPICAL PERFORMANCE (continued)

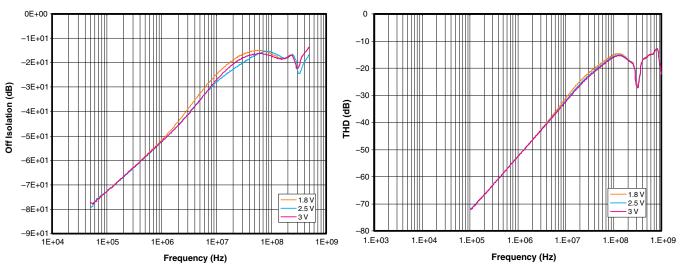


Figure 7. OFF Isolation and Crosstalk

Figure 8. Total Harmonic Distortion vs Frequency

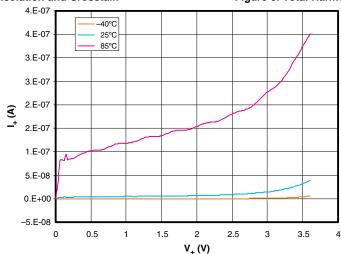


Figure 9. Power-Supply Current vs V₊

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TS3A24157 0.65-Ω DUAL SPDT ANALOG SWITCH DUAL-CHANNEL 2:1 MULTIPLEXER/DEMULTIPLEXER

SCDS208A-JUNE 2007-REVISED SEPTEMBER 2007

PIN DESCRIPTION

NO.	NAME	DESCRIPTION
1	NC1	Normally closed
2	NO1	Normally open
3	NC2	Normally closed
4	NO2	Normally open
5	GND	Ground
6	COM2	Common
7	IN2	Digital control to connect COM2 to NO2 or NC2
8	IN1	Digital control to connect COM1 to NO1 or NC1
9	COM1	Common
10	V_{+}	Power supply



PARAMETER DESCRIPTION

V _{NO} Voltage at NO Voltage at NO Voltage at NO Voltage at NO Resistance between COM and NC or COM and NO ports when the channel is ON fleesk Peak on-state resistance over a specified voltage range Afan Difference of f _{on} between the maximum and minimum value of f _{on} in a channel over the specified range of conditions Unifference between the maximum and minimum value of f _{on} in a channel over the specified range of conditions Mc(PWROFF) Unifference between the maximum and minimum value of f _{on} in a channel over the specified range of conditions Mc(PWROFF) Unifference value and volted to conditions Mc(PWROFF) Unifference value and volted to conditions Mc(PWROFF) Unifference value and volted value and volted value of	SYMBOL	DESCRIPTION
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Resistance between COM and NC or COM and NO ports when the channel is ON Peak on-state resistance over a specified voltage range Difference of from between channels in a specific device Funtion Difference between the maximum and minimum value of ron in a channel over the specified range of conditions Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the OFF state under worst-case input and output conditions NC(PINROFF) Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the OFF state under worst-case input and output conditions NC(PINROFF) Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the OFF state under worst-case input and output conditions NC(PINROFF) Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the OFF state under worst-case input and output conditions NC(PINROFF) Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the ON state and the output (COM) open Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the ON state and the output (COM) open Leakage current measured at the COM port, with the corresponding channel (NO to COM to NO or COM to NC) in the ON state and the output (NC or NO) open Commowner(F) Leakage current measured at the COM port during the power-down condition, V ₊ = 0 Whimmum input voltage for logic low for the control input (IN) VI, Maximum input voltage for logic low for the control input (IN) VI, Voltage at the control input (IN) VI, Voltage at the control input (IN) Turn-off time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM, NC, or NO) signal when the switch is turning OR. Leakage current measured at the control input (IN) Turn-off time for the switch. This parameter is measured under the specified range	V_{NC}	Voltage at NC
Peak On-state resistance over a specified voltage range Δr _{an} Difference of r _{an} between channels in a specific device fort(tital) Difference of r _{an} between channels in a specified device Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the OFF state under worst-case input and output conditions NC(FF)/WRDFP) Leakage current measured at the NC port during the power-down condition, V _a = 0 Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the OFF state under worst-case input and output conditions NC(DFF) Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the OFF state under worst-case input and output conditions NC(DW) Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the ON state and the output (COM) (COM) open Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the ON state and the output (NO pen Leakage current measured at the COM port during the power-down condition, V _a = 0 V ₁ (COM) open Leakage current measured at the COM port during the power-down condition, V _a = 0 V ₁ (COM) open Leakage current measured at the COM port during the power-down condition, V _a = 0 V ₁ (COM) open V ₁ (COM) open Leakage current measured at the COM port during the power-down condition, V _a = 0	V_{NO}	Voltage at NO
ΔΓαn Difference of r _{on} between channels in a specific device familiar Difference between the maximum and minimum value of r _{on} in a channel over the specified range of conditions MCiOFF Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the OFF state under worst-case input and output conditions MCiOFF Leakage current measured at the NC port during the power-down condition, V₂ = 0 Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the OFF state under worst-case input and output conditions MciOFF Leakage current measured at the NO port during the power-down condition, V₂ = 0 Leakage current measured at the NC port, with the corresponding channel (NO to COM) in the ON state and the output (COM) open Leakage current measured at the NC port, with the corresponding channel (NO to COM) in the ON state and the output (COM) open Leakage current measured at the COM port, with the corresponding channel (NO to COM) in the ON state and the output (NC or NO) open Looking No Leakage current measured at the COM port, with the corresponding channel (COM to NO or COM to NC) in the ON state and the output (NC or NO) open Looking No Minimum input voltage for logic how for the control input (IN) Vi Minimum input voltage for logic how for the control input (IN) Vi Voltage at the control input (NC) Vi Voltage a	r _{on}	Resistance between COM and NC or COM and NO ports when the channel is ON
Difference between the maximum and minimum value of r _{on} in a channel over the specified range of conditions	r _{peak}	Peak on-state resistance over a specified voltage range
Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the OFF state under worst-case input and output conditions No(IPWROFF) Leakage current measured at the NC port during the power-down condition, V ₊ = 0 Leakage current measured at the NC port, with the corresponding channel (NO to COM) in the OFF state under worst-case input and output conditions No(IPWROFF) Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the ON state and the output (COM) (COM) (COM) (COM) Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the ON state and the output (COM) open Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the ON state and the output (COM) open Leakage current measured at the COM port, with the corresponding channel (COM to NO or COM to NC) in the ON state and the output (NC or NO) open Leakage current measured at the COM port during the power-down condition, V ₊ = 0 V _H Minimum input voltage for logic high for the control input (IN) V _{IL} Maximum input voltage for logic low for the control input (IN) V _{IL} Voltage at the control input (IN) Turn-on time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM), NC, or NO) signal when the switch is turning ON. Torref Turn-off time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM), NC, or NO) signal when the switch is turning OFF. Beam Break-before-make time. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM), NC, or NO) signal when the switch is turning OFF. Cocomory Cocomory Capacitance at the NC port when the corresponding channel (NC to COM) is OFF Cocomory Capac	Δr _{on}	Difference of ron between channels in a specific device
NGCOFF) worst-case input and output conditions NGCPWROFF) Leakage current measured at the NC port, with the corresponding channel (NO to COM) in the OFF state under worst-case input and output conditions NGCOFF) Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the OFF state under worst-case input and output conditions NGCON) Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the ON state and the output (COM) open Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the ON state and the output (COM) open Leakage current measured at the COM port, with the corresponding channel (COM to NC or M to NC) in the ON state and the output (COM) open Leakage current measured at the COM port during the power-down condition, V ₊ = 0 ViH Minimum input voltage for logic high for the control input (IN) ViL Maximum input voltage for logic high for the control input (IN) ViL Voltage at the control input (IN) Leakage current measured at the control input (IN) Turn-on time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM, NC, or NO) signal when the switch is turning ON. Turn-off time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM, NC, or NO) signal when the switch is turning ON. Turn-off time for the switch This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM, NC, or NO) signal when the switch is turning ON. Turn-off time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM, NC, or NO) signal when the switch is turning ON. The Bre	r _{on(flat)}	Difference between the maximum and minimum value of ron in a channel over the specified range of conditions
Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the OFF state under worst-case input and output conditions Leakage current measured at the NO port during the power-down condition, V _* = 0 Leakage current measured at the NO port during the power-down condition, V _* = 0 Leakage current measured at the NO port, with the corresponding channel (NC to COM) in the ON state and the output (COM) open Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the ON state and the output (COM) open Leakage current measured at the COM port, with the corresponding channel (NO to COM) in the ON state and the output (NC or NO) open Leakage current measured at the COM port during the power-down condition, V _* = 0 ViH Minimum input voltage for logic high for the control input (IN) ViL Maximum input voltage for logic low for the control input (IN) ViJ Voltage at the control input (IN) ViJ Voltage at the control input (IN) In Leakage current measured at the control input (IN) In Turn-on time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM, NC, or NO) signal when the switch is turning ON. In Turn-off time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM, NC, or NO) signal when the switch is turning OFF. In the output of two adjacent analog channels (NC and NO) when the control signal changes state. Charge injection is a measurement of unwanted signal coupling from the control signal changes state. Charge injection is a measurement of unwanted signal coupling from the control signal changes state. Charge injection is a measurement of unwanted signal coupling from the control signal changes state. Charge injection is a measurement of unwanted signal coupling from the control signal changes state.	I _{NC(OFF)}	
NO(OFF) NO(OF	I _{NC(PWROFF)}	Leakage current measured at the NC port during the power-down condition, $V_{+} = 0$
Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the ON state and the output (COM) open Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the ON state and the output (COM) open Leakage current measured at the COM port, with the corresponding channel (COM to NO or COM to NC) in the ON state and the output (NC or NO) open Leakage current measured at the COM port during the power-down condition, V ₊ = 0 V _H Minimum input voltage for logic high for the control input (IN) V _L Maximum input voltage for logic low for the control input (IN) V _L Leakage current measured at the control input (IN) V _L Maximum input voltage for logic low for the control input (IN) V _L Leakage current measured at the control input (IN) V _L Leakage current measured at the control input (IN) I _{H+} I _L Leakage current measured at the control input (IN) Turn-on time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM, NC, or NO) signal when the switch is turning ON. Turn-off time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM, NC, or NO) signal when the switch is turning OFF. Break-before-make time. This parameter is measured under the specified range of conditions and by the propagation delay between the output of two adjacent analog channels (NC and NO) when the control signal changes state. Charge injection is a measurem of unwanted signal coupling from the control (IN) input to the analog (NC, NO, or COM) output. This is measured in countom (C) and measured by the total charge induced due to switching of the control input. Charge injection, Q _C = C _L × ΔV _{COM} , C _L is the load capacitance and ΔV _{COM} is the change in analog output voltage. Cho(OFF) Capacitance at the NC port when the co	I _{NO(OFF)}	
Nocion COM open	I _{NO(PWROFF)}	Leakage current measured at the NO port during the power-down condition, $V_{+} = 0$
ICOM(ON) ICOM) open Leakage current measured at the COM port, with the corresponding channel (COM to NO or COM to NC) in the ON state and the output (NC or NO) open	I _{NC(ON)}	
CCOM(ON) and the output (NC or NO) open	I _{NO(ON)}	
V _{IH} Minimum input voltage for logic high for the control input (IN) V _{IL} Maximum input voltage for logic low for the control input (IN) V _{IL} Voltage at the control input (IN) V _{IH} , I _{IL} Leakage current measured at the control input (IN) Turn-on time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM, NC, or NO) signal when the switch is turning ON. Turn-off time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM, NC, or NO) signal when the switch is turning ON. Break-before-make time. This parameter is measured under the specified range of conditions and by the propagation delay between the output of two adjacent analog channels (NC and NO) when the control signal changes state. Charge injection is a measurement of unwanted signal coupling from the control lin) input to the analog (NC, NO, or COM) output. This is measured in coulomb (C) and measured by the total charge induced due to switching of the control input. Charge injection, Q _C = C _L × ΔV _{COM} , C _L is the load capacitance and ΔV _{COM} is the change in analog output voltage. CNC(OFF) Capacitance at the NC port when the corresponding channel (NC to COM) is OFF CNC(ON) Capacitance at the NC port when the corresponding channel (NC to COM) is OFF CNC(ON) Capacitance at the NC port when the corresponding channel (NC to COM) is ON Capacitance at the NC port when the corresponding channel (NC to COM) is ON Capacitance at the NC port when the corresponding channel (NC to COM) is ON Capacitance at the NC port when the corresponding channel (NC to COM) is ON Capacitance of control input (IN) Olso OFF isolation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NC to COM or NO to COM) in the OFF channel (NC to	I _{COM(ON)}	Leakage current measured at the COM port, with the corresponding channel (COM to NO or COM to NC) in the ON state and the output (NC or NO) open
VIL Maximum input voltage for logic low for the control input (IN) V1 Voltage at the control input (IN) Int. IIL Leakage current measured at the control input (IN) ton Turn-on time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM, NC, or NO) signal when the switch is turning ON. toFF Turn-off time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM, NC, or NO) signal when the switch is turning OFF. teBM Break-before-make time. This parameter is measured under the specified range of conditions and by the propagation delay between the output of two adjacent analog channels (NC and NO) when the control signal changes state. QC Charge injection is a measurement of unwanted signal coupling from the control (IN) input to the analog (NC, NO, or COM) output. This is measured in coulomb (C) and measured by the total charge induced due to switching of the control input. Charge injection, Q _C = C _L × ΔV _{COM} , C _L is the load capacitance and ΔV _{COM} is the change in analog output voltage. CNCIOFF) Capacitance at the NC port when the corresponding channel (NC to COM) is OFF CNCION) Capacitance at the NO port when the corresponding channel (NC to COM) is ON CCOM(ON) Capacitance at the NO port when the corresponding channel (NC to COM) is ON	I _{COM(PWROFF)}	Leakage current measured at the COM port during the power-down condition, $V_{+} = 0$
V _I Voltage at the control input (IN) I _{IH} , I _{IL} Leakage current measured at the control input (IN) Turn-on time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM, NC, or NO) signal when the switch is turning ON. Turn-off time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM, NC, or NO) signal when the switch is turning OFL. I _B Break-before-make time. This parameter is measured under the specified range of conditions and by the propagation delay between the output of two adjacent analog channels (NC and NO) when the control signal changes state. Charge injection is a measurement of unwanted signal coupling from the control (IN) input to the analog (NC, NO, or COM) output. This is measured in coulomb (C) and measured by the total charge induced due to switching of the control input. Charge injection, Q _C = C _L × ΔV _{COM} , C _L is the load capacitance and ΔV _{COM} is the change in analog output voltage. C _{NC(OFF)} Capacitance at the NC port when the corresponding channel (NC to COM) is OFF C _{NC(ON)} Capacitance at the NC port when the corresponding channel (NC to COM) is ON C _{COM(ON)} Capacitance at the NO port when the corresponding channel (NO to COM) is ON C _{COM(ON)} Capacitance at the NO port when the corresponding channel (NO to COM) is ON C _{COM(ON)} Capacitance at the NO port when the corresponding channel (NO to COM) is ON C _{COM(ON)} Capacitance of control input (IN) O _{ISO} OFF isolation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NC to COM or NO to COM) in the OFF state. Crosstalk is a measurement of unwanted signal coupling from an ON channel to an OFF channel (NC to NO or NO to NO: NC). This is measured in a specific frequency in which the ga	V_{IH}	Minimum input voltage for logic high for the control input (IN)
Leakage current measured at the control input (IN) Turn-on time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM, NC, or NO) signal when the switch is turning ON. Turn-off time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM, NC, or NO) signal when the switch is turning ON. Turn-off time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM, NC, or NO) signal when the switch is turning OFF. Break-before-make time. This parameter is measured under the specified range of conditions and by the propagation delay between the output of two adjacent analog channels (NC and NO) when the control signal changes state. Charge injection is a measurement of unwanted signal coupling from the control (IN) input to the analog (NC, NO, or COM) output. This is measured in coulomb (C) and measured by the total charge induced due to switching of the control input. Charge injection, Q _C = C _L × ΔV _{COM} , C _L is the load capacitance and ΔV _{COM} is the change in analog output voltage. Cnc(OFF) Capacitance at the NC port when the corresponding channel (NC to COM) is OFF Cnc(ON) Capacitance at the NC port when the corresponding channel (NC to COM) is ON Capacitance at the NO port when the corresponding channel (NO to COM) is ON Capacitance at the NO port when the corresponding channel (NO to COM) is ON Com(ON) Capacitance at the COM port when the corresponding channel (NO to COM) is ON Copecitance at the COM port when the corresponding channel (NO to COM) is ON Copecitance at the COM port when the corresponding channel (NO to COM) is ON Copecitance at the COM port when the corresponding channel (NO to COM) is ON Capacitance at the COM port when the	V_{IL}	Maximum input voltage for logic low for the control input (IN)
Turn-on time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM, NC, or NO) signal when the switch is turning ON. Turn-off time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM, NC, or NO) signal when the switch is turning OFF. Break-before-make time. This parameter is measured under the specified range of conditions and by the propagation delay between the output of two adjacent analog channels (NC and NO) when the control signal changes state. Charge injection is a measurement of unwanted signal coupling from the control (IN) input to the analog (NC, NO, or COM) output. This is measured in coulomb (C) and measured by the total charge induced due to switching of the control input. Charge injection, Q _C = C _L × ΔV _{COM} , C _L is the load capacitance and ΔV _{COM} is the change in analog output voltage. CNC(OFF) Capacitance at the NC port when the corresponding channel (NC to COM) is OFF CNC(OFF) Capacitance at the NC port when the corresponding channel (NC to COM) is ON CCOM(ON) Capacitance at the NC port when the corresponding channel (NO to COM) is ON CCOM(ON) Capacitance at the NO port when the corresponding channel (NO to COM) is ON CCOM(ON) Capacitance at the COM port when the corresponding channel (NO to COM) is ON Capacitance of control input (IN) Olso OFF isolation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NC to COM or NO to COM) in the OFF state. X _{TALK} Crosstalk is a measurement of unwanted signal coupling from an ON channel to an OFF channel (NC to NO or NO to NO). This is measured in a specific frequency and in dB. Bandwidth of the switch. This is the frequency in which the gain of an ON channel is –3 dB below the DC gain. Total harmon	VI	Voltage at the control input (IN)
delay between the digital control (IN) signal and analog output (COM, NC, or NO) signal when the switch is turning ON. Turn-off time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM, NC, or NO) signal when the switch is turning OFF. Break-before-make time. This parameter is measured under the specified range of conditions and by the propagation delay between the output of two adjacent analog channels (NC and NO) when the control signal changes state. Charge injection is a measurement of unwanted signal coupling from the control (IN) input to the analog (NC, NO, or COM) output. This is measured in coulomb (C) and measured by the total charge induced due to switching of the control input. Charge injection, Q _C = C _L × ΔV _{COM} . C _L is the load capacitance and ΔV _{COM} is the change in analog output voltage. CNC(OFF) Capacitance at the NC port when the corresponding channel (NC to COM) is OFF CNO(OFF) Capacitance at the NC port when the corresponding channel (NC to COM) is OFF CNO(ON) Capacitance at the NO port when the corresponding channel (NC to COM) is ON CCOM(ON) Capacitance at the NO port when the corresponding channel (NC to COM) is ON CCOM(ON) Capacitance at the COM port when the corresponding channel (NC to COM) is ON Capacitance of control input (IN) Oiso OFF isolation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NC to COM or NO to COM) in the OFF state. XTALK Crosstalk is a measurement of unwanted signal coupling from an ON channel is –3 dB below the DC gain. Total harmonic distortion describes the signal distortion caused by the analog switch. This is defined as the ratio of root mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental harmonic.	I _{IH} , I _{IL}	Leakage current measured at the control input (IN)
delay between the digital control (IN) signal and analog output (COM, NC, or NO) signal when the switch is turning OFF. Break-before-make time. This parameter is measured under the specified range of conditions and by the propagation delay between the output of two adjacent analog channels (NC and NO) when the control signal changes state. Charge injection is a measurement of unwanted signal coupling from the control (IN) input to the analog (NC, NO, or COM) output. This is measured in coulomb (C) and measured by the total charge induced due to switching of the control input. Charge injection, Q _C = C _L × ΔV _{COM} , C _L is the load capacitance and ΔV _{COM} is the change in analog output voltage. C _{NC(OFF)} Capacitance at the NC port when the corresponding channel (NC to COM) is OFF C _{NC(ON)} Capacitance at the NC port when the corresponding channel (NC to COM) is ON C _{COM(ON)} Capacitance at the NO port when the corresponding channel (NO to COM) is ON C _{COM(ON)} Capacitance at the COM port when the corresponding channel (NO to COM) is ON C _{COM(ON)} Capacitance at the COM port when the corresponding channel (COM to NC or COM to NO) is ON C ₁ Capacitance of control input (IN) O ₁ O ₁ O ₁ O ₂ Crosstalk is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NC to COM) in the OFF state. X ₁ X ₁ X ₁ X ₁ X ₁ X ₁ Total harmonic distortion describes the signal distortion caused by the analog switch. This is defined as the ratio of root mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental harmonic.	t _{ON}	
delay between the output of two adjacent analog channels (NC and NO) when the control signal changes state. Charge injection is a measurement of unwanted signal coupling from the control (IN) input to the analog (NC, NO, or COM) output. This is measured in coulomb (C) and measured by the total charge induced due to switching of the control input. Charge injection, Q _C = C _L × ΔV _{COM} , C _L is the load capacitance and ΔV _{COM} is the change in analog output voltage. C _{NC(OFF)} Capacitance at the NC port when the corresponding channel (NC to COM) is OFF C _{NO(ON)} Capacitance at the NC port when the corresponding channel (NC to COM) is ON C _{NO(ON)} Capacitance at the NO port when the corresponding channel (NC to COM) is ON C _{COM(ON)} Capacitance at the NO port when the corresponding channel (NO to COM) is ON C _{COM(ON)} Capacitance at the COM port when the corresponding channel (COM to NC or COM to NO) is ON C ₁ Capacitance of control input (IN) O ₁ O ₁ O ₁ O ₁ O ₂ O ₃ Crosstalk is a measurement of unwanted signal coupling from an ON channel to an OFF channel (NC to NO or NO to NC). This is measured in a specific frequency and in dB. BW Bandwidth of the switch. This is the frequency in which the gain of an ON channel is –3 dB below the DC gain. Total harmonic distortion describes the signal distortion caused by the analog switch. This is defined as the ratio of root mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental harmonic.	t _{OFF}	
COM) output. This is measured in coulomb (C) and measured by the total charge induced due to switching of the control input. Charge injection, Q _C = C _L × ΔV _{COM} , C _L is the load capacitance and ΔV _{COM} is the change in analog output voltage. C _{NC(OFF)} Capacitance at the NC port when the corresponding channel (NC to COM) is OFF C _{NO(ON)} Capacitance at the NC port when the corresponding channel (NO to COM) is ON Capacitance at the NC port when the corresponding channel (NO to COM) is ON Capacitance at the NO port when the corresponding channel (NO to COM) is ON Capacitance at the COM port when the corresponding channel (COM to NC or COM to NO) is ON Capacitance at the COM port when the corresponding channel (COM to NC or COM to NO) is ON Capacitance of control input (IN) O _{ISO} OFF isolation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NC to COM or NO to COM) in the OFF state. X _{TALK} Crosstalk is a measurement of unwanted signal coupling from an ON channel to an OFF channel (NC to NO or NO to NC). This is measured in a specific frequency and in dB. BW Bandwidth of the switch. This is the frequency in which the gain of an ON channel is –3 dB below the DC gain. Total harmonic distortion describes the signal distortion caused by the analog switch. This is defined as the ratio of root mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental harmonic.	t _{BBM}	
C _{NO(OFF)} Capacitance at the NO port when the corresponding channel (NO to COM) is OFF C _{NC(ON)} Capacitance at the NC port when the corresponding channel (NO to COM) is ON C _{NO(ON)} Capacitance at the NO port when the corresponding channel (NO to COM) is ON C _{COM(ON)} Capacitance at the COM port when the corresponding channel (COM to NC or COM to NO) is ON C _{COM(ON)} Capacitance of control input (IN) O _{ISO} OFF isolation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NC to COM or NO to COM) in the OFF state. Crosstalk is a measurement of unwanted signal coupling from an ON channel to an OFF channel (NC to NO or NO to NC). This is measured in a specific frequency and in dB. Bandwidth of the switch. This is the frequency in which the gain of an ON channel is –3 dB below the DC gain. Total harmonic distortion describes the signal distortion caused by the analog switch. This is defined as the ratio of root mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental harmonic.	Q_C	COM) output. This is measured in coulomb (C) and measured by the total charge induced due to switching of the control
C _{NC(ON)} Capacitance at the NC port when the corresponding channel (NC to COM) is ON C _{NO(ON)} Capacitance at the NO port when the corresponding channel (NO to COM) is ON C _{COM(ON)} Capacitance at the COM port when the corresponding channel (COM to NC or COM to NO) is ON C _{COM(ON)} Capacitance of control input (IN) O _{ISO} OFF isolation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NC to COM or NO to COM) in the OFF state. X _{TALK} Crosstalk is a measurement of unwanted signal coupling from an ON channel to an OFF channel (NC to NO or NO to NC). This is measured in a specific frequency and in dB. BW Bandwidth of the switch. This is the frequency in which the gain of an ON channel is –3 dB below the DC gain. Total harmonic distortion describes the signal distortion caused by the analog switch. This is defined as the ratio of root mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental harmonic.	C _{NC(OFF)}	Capacitance at the NC port when the corresponding channel (NC to COM) is OFF
C _{NO(ON)} Capacitance at the NO port when the corresponding channel (NO to COM) is ON C _{COM(ON)} Capacitance at the COM port when the corresponding channel (COM to NC or COM to NO) is ON C _I Capacitance of control input (IN) O _{ISO} OFF isolation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NC to COM or NO to COM) in the OFF state. X _{TALK} Crosstalk is a measurement of unwanted signal coupling from an ON channel to an OFF channel (NC to NO or NO to NC). This is measured in a specific frequency and in dB. BW Bandwidth of the switch. This is the frequency in which the gain of an ON channel is –3 dB below the DC gain. Total harmonic distortion describes the signal distortion caused by the analog switch. This is defined as the ratio of root mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental harmonic.	C _{NO(OFF)}	Capacitance at the NO port when the corresponding channel (NO to COM) is OFF
C _{NO(ON)} Capacitance at the NO port when the corresponding channel (NO to COM) is ON C _{COM(ON)} Capacitance at the COM port when the corresponding channel (COM to NC or COM to NO) is ON C _I Capacitance of control input (IN) O _{ISO} OFF isolation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NC to COM or NO to COM) in the OFF state. Crosstalk is a measurement of unwanted signal coupling from an ON channel to an OFF channel (NC to NO or NO to NC). This is measured in a specific frequency and in dB. BW Bandwidth of the switch. This is the frequency in which the gain of an ON channel is –3 dB below the DC gain. Total harmonic distortion describes the signal distortion caused by the analog switch. This is defined as the ratio of root mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental harmonic.	C _{NC(ON)}	Capacitance at the NC port when the corresponding channel (NC to COM) is ON
CCOM(ON) Capacitance at the COM port when the corresponding channel (COM to NC or COM to NO) is ON Capacitance of control input (IN) OISO OFF isolation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NC to COM or NO to COM) in the OFF state. Crosstalk is a measurement of unwanted signal coupling from an ON channel to an OFF channel (NC to NO or NO to NC). This is measured in a specific frequency and in dB. BW Bandwidth of the switch. This is the frequency in which the gain of an ON channel is –3 dB below the DC gain. Total harmonic distortion describes the signal distortion caused by the analog switch. This is defined as the ratio of root mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental harmonic.	C _{NO(ON)}	Capacitance at the NO port when the corresponding channel (NO to COM) is ON
OFF isolation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NC to COM or NO to COM) in the OFF state. XTALK Crosstalk is a measurement of unwanted signal coupling from an ON channel to an OFF channel (NC to NO or NO to NC). This is measured in a specific frequency and in dB. BW Bandwidth of the switch. This is the frequency in which the gain of an ON channel is –3 dB below the DC gain. Total harmonic distortion describes the signal distortion caused by the analog switch. This is defined as the ratio of root mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental harmonic.	C _{COM(ON)}	Capacitance at the COM port when the corresponding channel (COM to NC or COM to NO) is ON
frequency, with the corresponding channel (NC to COM or NO to COM) in the OFF state. X _{TALK} Crosstalk is a measurement of unwanted signal coupling from an ON channel to an OFF channel (NC to NO or NO to NC). This is measured in a specific frequency and in dB. Bandwidth of the switch. This is the frequency in which the gain of an ON channel is –3 dB below the DC gain. Total harmonic distortion describes the signal distortion caused by the analog switch. This is defined as the ratio of root mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental harmonic.	C _I	Capacitance of control input (IN)
NC). This is measured in a specific frequency and in dB. Bandwidth of the switch. This is the frequency in which the gain of an ON channel is –3 dB below the DC gain. Total harmonic distortion describes the signal distortion caused by the analog switch. This is defined as the ratio of root mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental harmonic.	O _{ISO}	
Total harmonic distortion describes the signal distortion caused by the analog switch. This is defined as the ratio of root mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental harmonic.	X _{TALK}	
THD mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental harmonic.	BW	Bandwidth of the switch. This is the frequency in which the gain of an ON channel is -3 dB below the DC gain.
I ₊ Static power-supply current with the control (IN) pin at V ₊ or GND	THD	mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental
	I ₊	Static power-supply current with the control (IN) pin at V ₊ or GND





PARAMETER MEASUREMENT INFORMATION

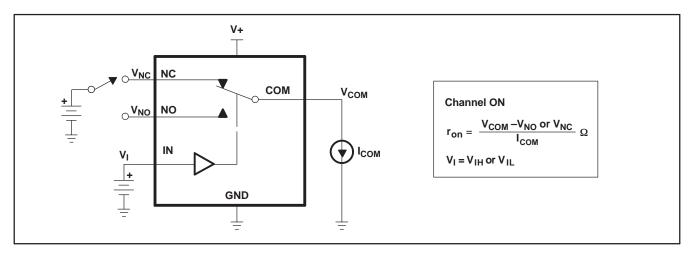


Figure 10. ON-State Resistance (ron)

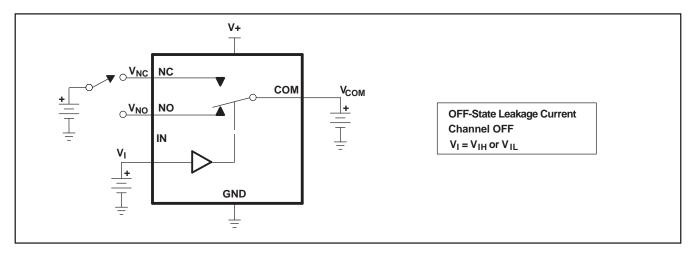


Figure 11. OFF-State Leakage Current (I_{NC(OFF)}, I_{NO(PWROFF)}, I_{NO(PWROFF)}, I_{COM(PWROFF)})

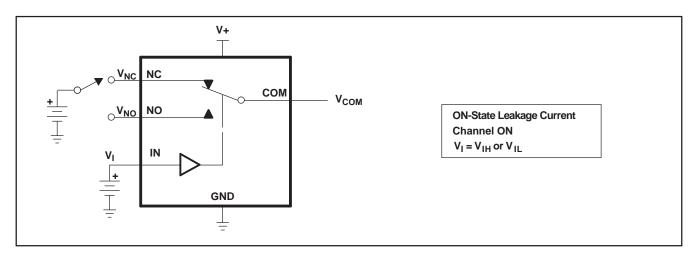


Figure 12. ON-State Leakage Current ($I_{COM(ON)}$, $I_{NC(ON)}$, $I_{NO(ON)}$)



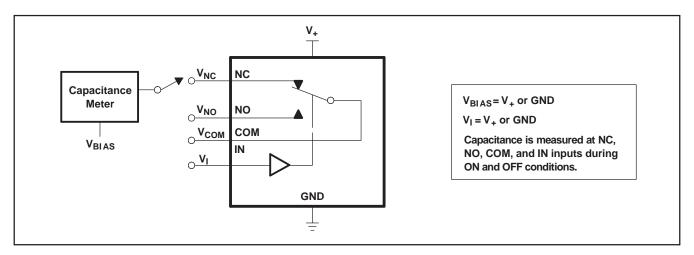
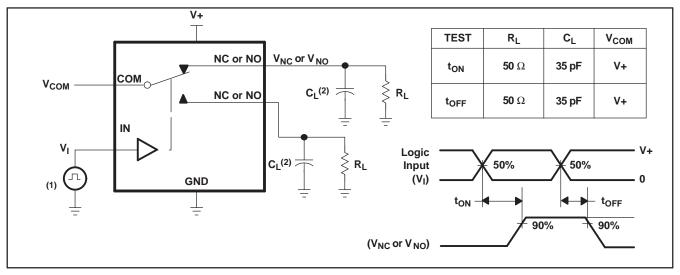


Figure 13. Capacitance (C_I, $C_{COM(ON)}$, $C_{NC(OFF)}$, $C_{NO(OFF)}$, $C_{NC(ON)}$, $C_{NO(ON)}$)

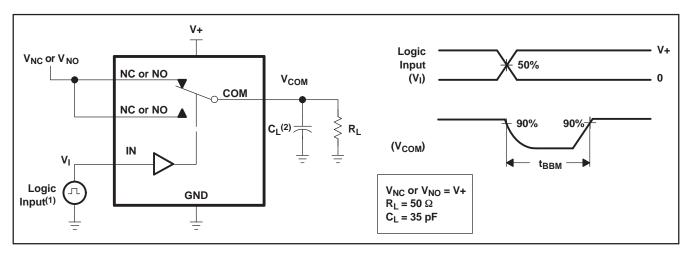


- A. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_r < 5 \text{ ns}$, $t_r < 5 \text{ ns}$.
- B. C_L includes probe and jig capacitance.

Figure 14. Turn-On (t_{ON}) and Turn-Off Time (t_{OFF})







- A. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_f < 5 \text{ ns}$, $t_f < 5 \text{ ns}$.
- B. C_L includes probe and jig capacitance.

Figure 15. Break-Before-Make Time (t_{BBM})

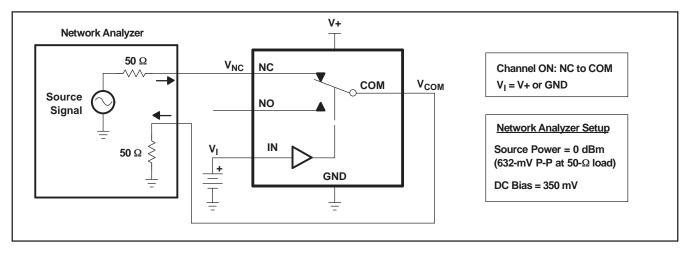


Figure 16. Bandwidth (BW)



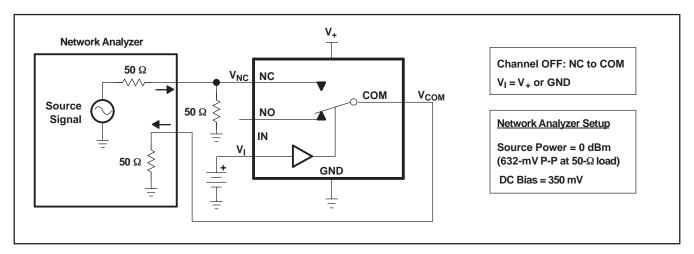


Figure 17. OFF Isolation (O_{ISO})

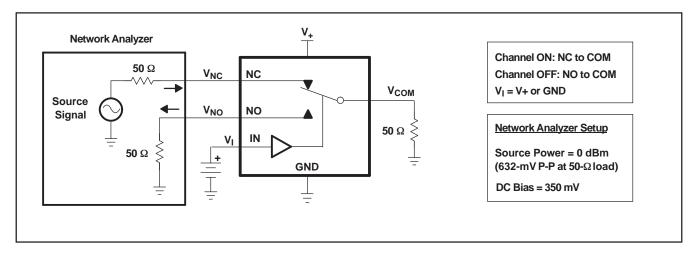
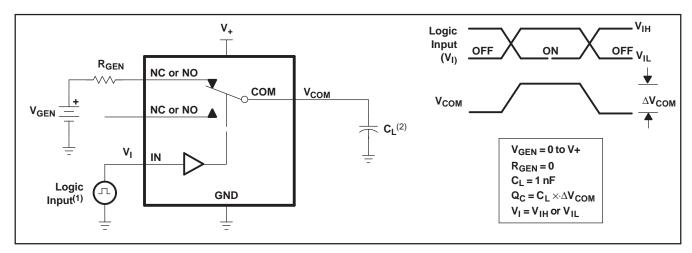


Figure 18. Crosstalk (X_{TALK})

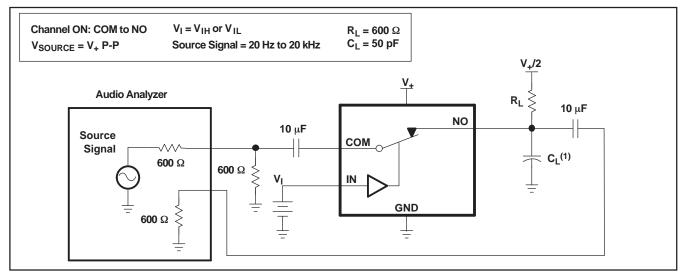






- A. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_f < 5$ ns, $t_f < 5$ ns.
- B. C_L includes probe and jig capacitance.

Figure 19. Charge Injection (Q_C)



A. C_L includes probe and jig capacitance.

Figure 20. Total Harmonic Distortion (THD)

19-Nov-2012

PACKAGING INFORMATION

Orderable Device	Status	Package Type	_		Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Samples
	(1)		Drawing			(2)		(3)	(Requires Login)
TS3A24157DGSR	ACTIVE	VSSOP	DGS	10	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TS3A24157DGSRG4	ACTIVE	VSSOP	DGS	10	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TS3A24157RSER	ACTIVE	UQFN	RSE	10	3000	TBD	Call TI	Call TI	
TS3A24157RSERG4	ACTIVE	UQFN	RSE	10	3000	TBD	Call TI	Call TI	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS3A24157DGSR	VSSOP	DGS	10	2500	330.0	12.4	5.3	3.3	1.3	8.0	12.0	Q1

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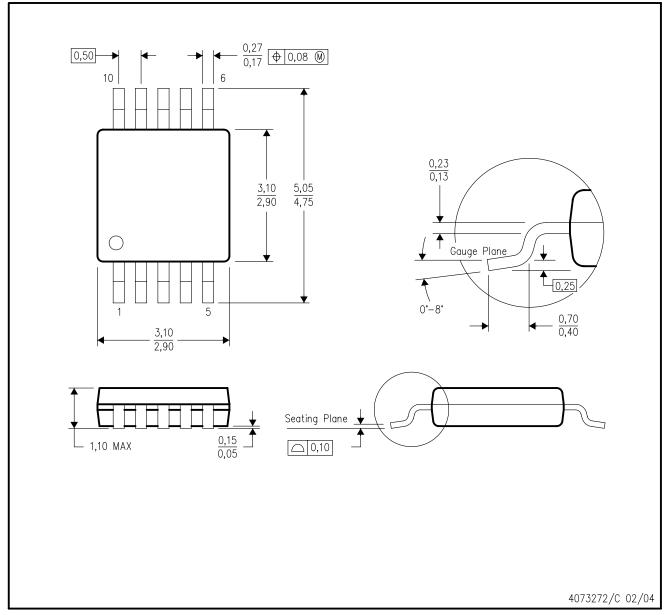


*All dimensions are nominal

Device	Device Package Type		Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
TS3A24157DGSR	VSSOP	DGS	10	2500	346.0	346.0	35.0	

DGS (S-PDSO-G10)

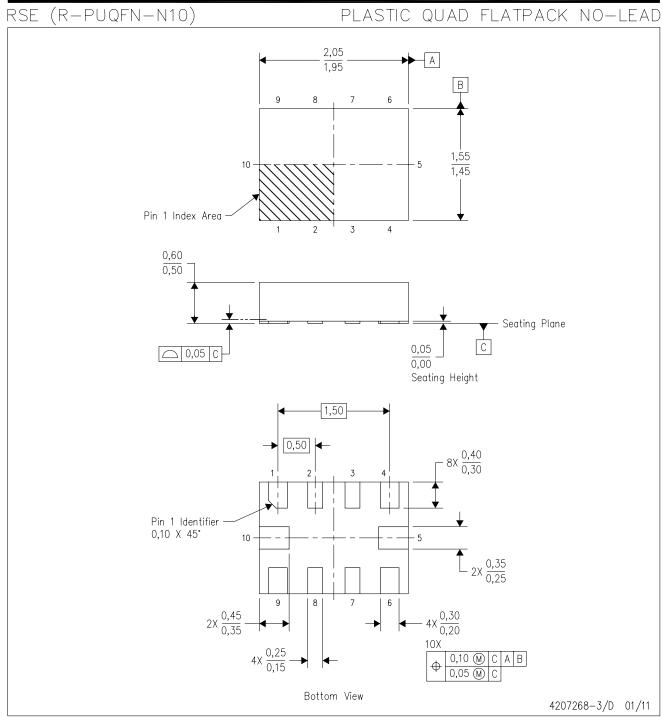
PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. Falls within JEDEC MO-187 variation BA.





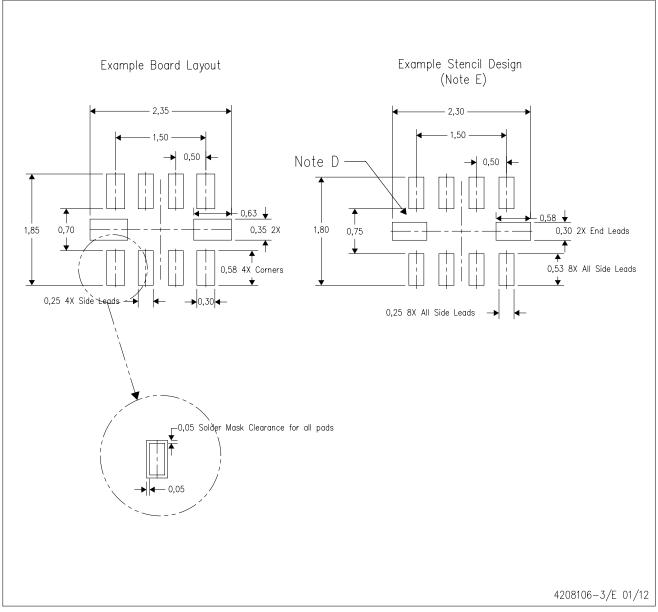
NOTES: All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
 C. QFN (Quad Flatpack No-Lead) package configuration.
 D. This package complies to JEDEC MO-288 variation UEFD.



RSE (R-PUQFN-N10)

PLASTIC QUAD FLATPACK NO-LEAD



- NOTES: A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Publication IPC-7351 is recommended for alternate designs.
 - D. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.
 - E. Maximum stencil thickness 0,127 mm (5 mils). All linear dimensions are in millimeters.
 - F. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
 - G. Side aperture dimensions over-print land for acceptable area ratio > 0.66. Customer may reduce side aperture dimensions if stencil manufacturing process allows for sufficient release at smaller opening.



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